

H5N2513PL

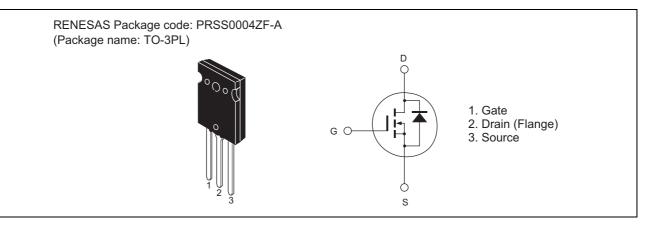
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1243-0200 Rev.2.00 May 13, 2009

Features

- Low on-resistance
- High speed switching
- Built-in fast recovery diode

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	250	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	100	A
Drain peak current	Note1 I _{D (pulse)}	400	A
Body-drain diode reverse drain current	I _{DR}	100	A
Body-drain diode reverse drain	Note1 I _{DR (pulse)}	400	A
peak current			
Avalanche current	I _{AP} Note3	100	A
Avalanche energy	E _{AR} Note3	625	mJ
Channel dissipation	Pch Note2	250	W
Channel to case thermal impedance	θch-c	0.5	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

2. Value at Tc = 25°C

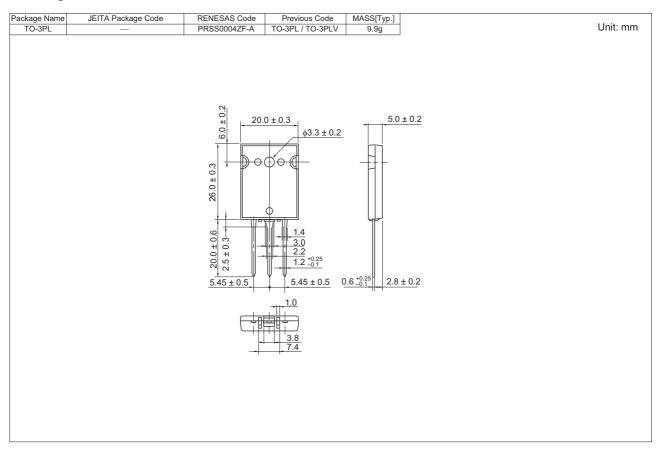
3. STch = 25° C, Tch $\leq 150^{\circ}$ C

Electrical Characteristics

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to Source breakdown voltage	V _{(BR)DSS}	250	_		V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}		_	10	μΑ	$V_{DS} = 250 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}		_	±0.1	μA	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	2.0	_	4.0	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Forward transfer admittance	y _{fs}	39	65	_	S	$I_D = 50 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Static drain to source on state resistance	R _{DS(on)}	—	0.020	0.026	Ω	$I_D = 50 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss		9300		pF	$V_{DS} = 25 \text{ V}, \text{ V}_{GS} = 0,$ f = 1 MHz
Output capacitance	Coss	_	1200	_	pF	
Reverse transfer capacitance	Crss	_	280	_	pF	
Turn-on delay time	t _{d(on)}	_	90	—	ns	$\begin{split} I_D &= 50 \text{ A}, V_{GS} = 10 \text{ V}, \\ R_L &= 2.5 \Omega, \text{Rg} = 10 \Omega \end{split}$
Rise time	tr	_	420	—	ns	
Turn-off delay time	t _{d(off)}	_	550	—	ns	
Fall time	t _f		400	—	ns	
Total gate charge	Qg	—	330	—	nC	$V_{DD} = 200 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$
Gate to source charge	Qgs		45	—	nC	I _D = 100 A
Gate to drain charge	Qgd		175	—	nC	
Body-drain diode forward voltage	V _{DF}	_	1.2	1.8	V	$I_F = 100 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t _{rr}	—	210	—	ns	I _F = 100 A, V _{GS} = 0 diF/dt = 100 A/μs

Notes: 4. Pulse test

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
H5N2513PL-E	250 pcs.	Box (Tube)

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